

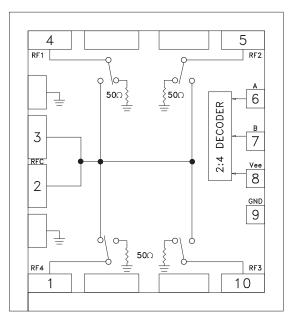
## GaAs MMIC SP4T NON-REFLECTIVE SWITCH, DC - 8 GHz

### **Typical Applications**

The HMC344 is ideal for:

- Telecom Infrastructure
- Microwave Radio & VSAT
- Military & Space
- Test Instrumentation

#### **Functional Diagram**



#### Features

Broadband Performance: DC - 8 GHz Non-Reflective Topology Low Insertion Loss: 1.8 dB @ 6 GHz Integrated 2:4 TTL Decoder Small Size: 1.08 x 1.05 x 0.10 mm

#### **General Description**

The HMC344 is a broadband non-reflective GaAs MESFET SP4T switch chip. Covering DC to 8 GHz, this switch offers high isolation, low insertion loss, and a compact form factor. This switch also includes an on board binary decoder circuit which reduces the number of required logic control lines to two. The switch operates using a negative control voltage of 0/-5V, and requires a fixed bias of -5V. All data is tested with the chip in a 50 Ohm test fixture connected via 0.025 mm (1 mil) diameter wire bonds of minimal length 0.31 mm (12 mils). This SP4T switch is also available in SMT packaged form as the HMC344LC3.

#### Electrical Specifications, $T_A = +25^{\circ}$ C, With 0/-5V Control, Vee= -5V, 50 Ohm System

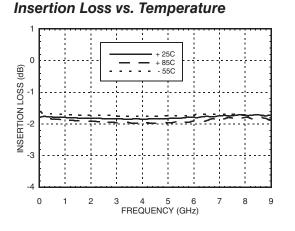
| Parameter   |             | Frequency  | Min.                 | Тур.                 | Max.       | Units                |
|---|-------------|--|----------------------|----------------------|------------|----------------------|
| Insertion Loss  |             | DC - 6.0 GHz<br>DC - 8.0 GHz                                 |                      | 1.8<br>1.9           | 2.1<br>2.2 | dB<br>dB             |
| Isolation   |             | DC - 2.0 GHz<br>DC - 4.0 GHz<br>DC - 6.0 GHz<br>DC - 8.0 GHz | 44<br>37<br>34<br>30 | 49<br>42<br>39<br>35 |            | dB<br>dB<br>dB<br>dB |
| Return Loss   | "On State"  | DC - 2.0 GHz<br>DC - 8.0 GHz                                 | 10<br>7              | 14<br>10             |            | dB<br>dB             |
| Return Loss   | "Off State" | DC - 8.0 GHz   | 7                    | 10                   |            | dB                   |
| Input Power for 1 dB Compression  |             | 0.5 - 8.0 GHz  | 17                   | 21                   |            | dBm                  |
| Input Third Order Intercept<br>(Two-Tone Input Power= +7 dBm Each Tone)                   |             | 0.5 - 8.0 GHz  | 37                   | 40                   |            | dBm                  |
| Switching Characteristics<br>tRISE, tFALL (10/90% RF)<br>tON, tOFF (50% CTL to 10/90% RF) |             | DC - 8.0 GHz   |                      | 35<br>150            |            | ns<br>ns             |

For price, delivery, and to place orders, please contact Hittite Microwave Corporation: 20 Alpha Road, Chelmsford, MA 01824 Phone: 978-250-3343 Fax: 978-250-3373 Order On-line at www.hittite.com

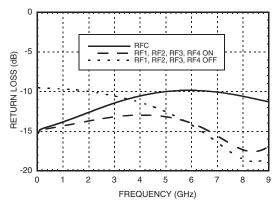


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Isolation

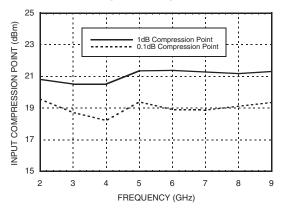


**Return Loss** 

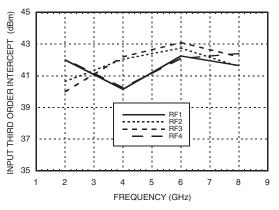


RF1 RF2 RF3 -20 . . **ISOLATION (dB)** RF4 40 -60 -80 4 5 6 FREQUENCY (GHz) 8 9 0 1 2 3 7

0.1 and 1 dB Input Compression Point



#### Input Third Order Intercept Point



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#### Absolute Maximum Ratings

| Bias Voltage Range (Vee)                    | -7V              |  |
|---|------------------|--|
| Control Voltage Range (A & B)               | Vee -0.5V to +1V |  |
| Channel Temperature                         | 150 °C           |  |
| Thermal Resistance<br>(Insertion Loss Path) | 143 °C/W         |  |
| Thermal Resistance<br>(Terminated Path)     | 1,030 °C/W       |  |
| Storage Temperature                         | -65 to +150 °C   |  |
| Operating Temperature                       | -55 to +85 °C    |  |
| Maximum Input Power                         | +24 dBm          |  |
| ESD Sensitivity (HBM)                       | Class 1A         |  |

#### Truth Table

| Control Input |      | Signal Path State |  |
|---------------|------|-------------------|--|
| A             | В    | RF COM to:        |  |
| High          | High | RF1               |  |
| Low           | High | RF2               |  |
| High          | Low  | RF3               |  |
| Low           | Low  | RF4               |  |

#### **Bias Voltage & Current**

| Vee Range = -5 Vdc ±10%   |   |                   |  |
|---------------------------|---|-------------------|--|
| Vee Idd (Typ)<br>(V) (mA) |   | ldd (Max)<br>(mA) |  |
| -5                        | 3 | 6                 |  |



#### ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

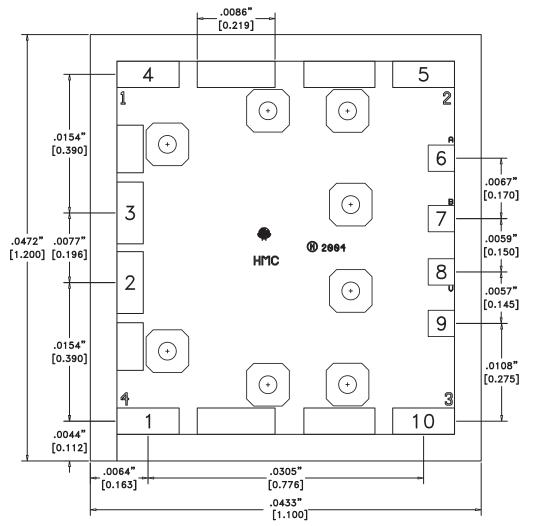
### **TTL/CMOS Control Voltages**

| State | Bias Condition            |
|-------|---------------------------|
| Low   | -3V to 0 Vdc @ 60 uA Typ. |
| High  | -5 to 4.2 Vdc @ 5 uA Typ. |



## GaAs MMIC SP4T NON-REFLECTIVE SWITCH, DC - 8 GHz

#### **Outline Drawing**



#### **Die Packaging Information**<sup>[1]</sup>

| Standard           | Alternate |
|--------------------|-----------|
| WP-2 (Waffle Pack) | [2]       |

[1] Refer to the "Packaging Information" section for die packaging dimensions. [2] For alternate packaging information contact Hittite

Microwave Corporation.

NOTES:

- 1. DIMENSIONS IN INCHES [MILLIMETERS].
- 2. DIE THICKNESS IS 0.004".
- 3. TYPICAL BOND PAD IS 0.004" SQUARE.
- 4. TYPICAL BOND PAD SPACING IS 0.006" CENTER TO CENTER.
- 5. BOND PAD METALLIZATION: GOLD.
- 6. BACKSIDE METALLIZATION: GOLD.
- 7. BACKSIDE METAL IS GROUND.
- 8. NO CONNECTION REQUIRED FOR UNLABELED BOND PADS.

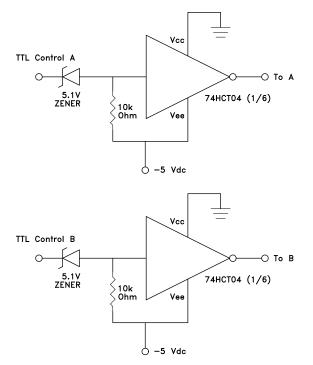


## GaAs MMIC SP4T NON-REFLECTIVE SWITCH, DC - 8 GHz

#### **Pad Descriptions**

| Pad Number           | Function                   | Description  | Interface Schematic |  |
|----------------------|----------------------------|--|---------------------|--|
| 1, 2, 3,<br>4, 5, 10 | RF4, RFC, RF1,<br>RF2, RF3 | These pads are DC coupled and matched to 50 Ohms.<br>Blocking capacitors are required. |                     |  |
| 6                    | A                          | See truth table and control voltage table.   | А,В О               |  |
| 7                    | В                          | See truth table and control voltage table.   | ↓ =<br>∨Vee         |  |
| 8                    | Vee                        | Supply Voltage -5.0 Vdc ±10%   |                     |  |
| 9, Die<br>Bottom     | GND                        | Die bottom and pad must be connected to RF/DC ground.                                  |                     |  |

### TTL Interface Circuit



#### Note:

Control inputs A and B can be driven directly with TTL logic with -5 Volts applied to the HCT logic gates Vee pin and to Vee (pad) of the RF Switch.

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#### Assembly Diagram

